

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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TECHNICAL DATA
DATA SHEET D0114 REV. –
SILICON SCHOTTKY RECTIFIER DIE
Applications:

- Switching Power Supply • Converters • Free-Wheeling Diodes • Polarity Protection Diode

Features:

- Ultra low Reverse Leakage Current
- Soft Reverse Recovery at Low and High Temperature
- Very Low Forward Voltage Drop
- Low Power Loss, High Efficiency
- High Surge Capacity
- Guard Ring for Enhanced Durability and Long Term Reliability
- Guaranteed Reverse Avalanche Characteristics
- Electrically / Mechanically Stable during and after Packaging

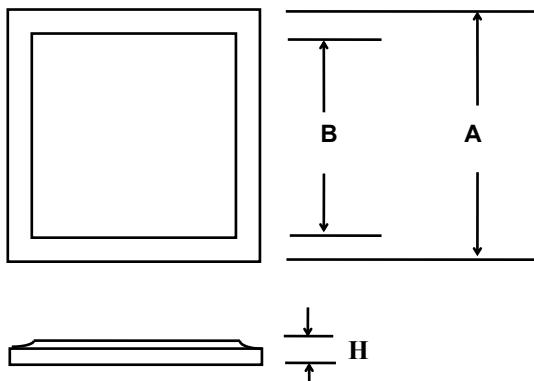
Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	200	V
Average Forward Current	$I_{F(AV)}$	50% duty cycle, rectangular wave form	15	A
Peak One Cycle Non-Repetitive Surge Current	I_{FSM}	8.3 ms, Sine pulse ⁽¹⁾	230	A
Junction Temperature	T_J	-	-55 to +200	°C
Storage Temperature	T_{stg}	-	-55 to +200	°C

Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Forward Voltage Drop	V_{F1}	@ 15A, Pulse, $T_J = 25$ °C	0.92	V
	V_{F2}	@ 15A, Pulse, $T_J = 125$ °C	0.76	V
Reverse Current	I_{R1}	@ $V_R = 200$ V, Pulse, $T_J = 25$ °C	0.35	mA
	I_{R2}	@ $V_R = 200$ V, Pulse, $T_J = 125$ °C	8	mA
Junction Capacitance	C_T	@ $V_R = 5$ V, $T_C = 25$ °C $f_{SIG} = 1$ MHz, $V_{SIG} = 50$ mV (p-p)	300	pF

(1) in SHD package

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Mechanical Dimensions: In Inches (mm)


Bottom side metallization Ag-5KÅ minimum
 Top side metallization Ag-25KÅ minimum
 Bottom side is cathode, top side is anode
 Dimension H = 0.0105 ± 0.001 (0.27 \pm 0.026) (It can be customized according to customer requirements)

A	B
0.125 ± 0.003 (3.18 \pm 0.08)	0.116 ± 0.003 (2.95 \pm 0.08)

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